

N-Channel CICLON NexFET™ Power MOSFETs CSD16411Q3

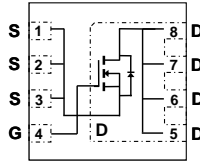


Features

- Ultra Low Qg & Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free



QFN 3.3mm x 3.3mm Plastic Package



Top View

Product Summary

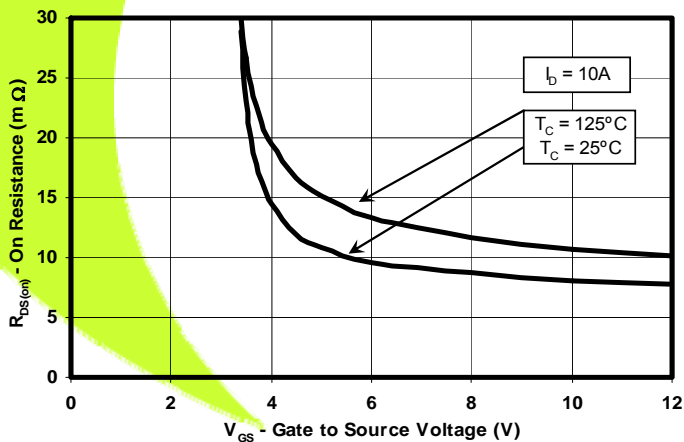
V_{DS}	25	V
Q_g	2.9	nC
Q_{gd}	0.7	nC
$R_{DS(on)}$	$V_{GS}=4.5V$	12 m Ω
	$V_{GS}=10V$	8 m Ω
V_{th}	2.0	V

Maximum Values ($T_A = 25^\circ C$ unless otherwise stated)

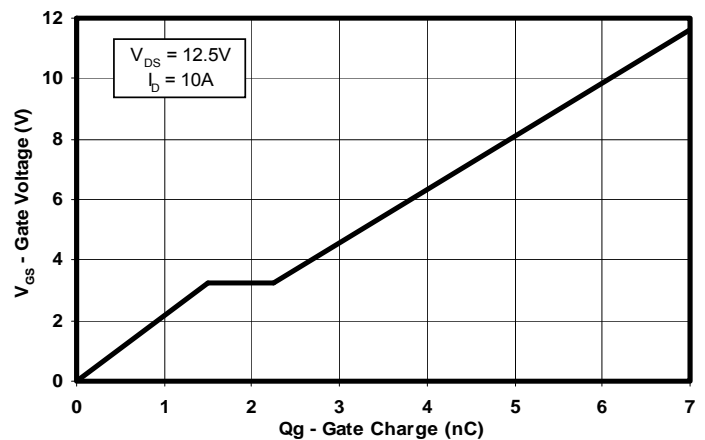
Symbol	Parameter	Value	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	V
I_b	Continuous Drain Current, $T_C = 25^\circ C$	56	A
	Continuous Drain Current ¹	14	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ C^2$	138	A
P_D	Power Dissipation ¹	2.7	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ C$
E_{AS}	Avalanche Energy, single pulse $I_D=18A, L = 0.1mH, R_G = 25\Omega$	16	mJ

1. $R_{\theta JA} = 47^\circ C/W$ on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
2. See Figure 10

$R_{DS(on)}$ vs. V_{GS}



Gate Charge



Ordering Information

Type	Package	Package Media	Qty	Ship
CSD16411Q3	QFN 3X3 Plastic Package	13 inch reel	2500	Tape and Reel

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Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25	—	—	V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$	—	—	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = 16V$	—	—	100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.7	2.0	2.3	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 10A$	—	12.0	15.0	$m\Omega$
		$V_{GS} = 10V, I_D = 10A$	—	8.0	10.0	$m\Omega$
g_{fs}	Transconductance	$V_{DS} = 15V, I_D = 10A$	—	30	—	S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V$ $f = 1MHz$	—	440	570	pF
C_{OSS}	Output Capacitance		—	330	430	pF
C_{RSS}	Reverse Transfer Capacitance		—	33	43	pF
R_g	Series Gate Resistance		—	0.6	—	Ω
Q_g	Gate Charge Total (4.5V)	$V_{DS} = 12.5V, I_D = 10A$	—	2.9	3.8	nC
Q_{gd}	Gate Charge Gate to Drain		—	0.7	—	nC
Q_{gs}	Gate Charge Gate to Source		—	1.5	—	nC
$Q_{g(th)}$	Gate Charge at V_{th}		—	0.9	—	nC
Q_{OSS}	Output Charge	$V_{DS} = 12.5V, V_{GS} = 0V$	—	6.5	—	nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 12.5V$ $V_{GS} = 4.5V, I_D = 10A$ $R_G = 15\Omega$	—	8.0	—	ns
t_r	Rise Time		—	18	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	6.8	—	ns
t_f	Fall Time		—	8.5	—	ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_S = 10A, V_{GS} = 0V$	—	0.85	1.0	V
Q_{rr}	Reverse Recovery Charge	$V_{dd} = 12.5V, I_F = 10A,$ $di/dt = 300A/\mu s$	—	11.7	—	nC
t_{rr}	Reverse Recovery Time	$V_{dd} = 12.5V, I_F = 10A,$ $di/dt = 300A/\mu s$	—	15.5	—	ns

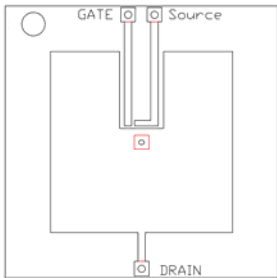
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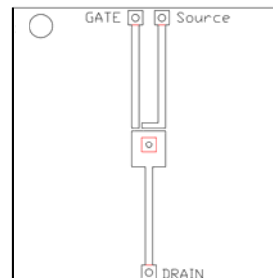
Thermal Characteristics (T_C = 25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Units
Thermal Characteristics					
R _{θJC}	Thermal Resistance Junction to Case ³	—	—	3.5	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ^{3,4}	—	—	59	°C/W

- R_{θJC} is determined with the device mounted on a 1in square 2 oz. Cu pad on a 1.5x1.5 in .060in thick FR4 board. R_{θJC} is guaranteed by design while R_{θca} is determined by the user's board design.
- Device mounted on FR4 Material with 1in² of 2 oz. Cu.



Max R_{θJA} = 59 °C/W when
mounted on 1in² of
2 oz. Cu.



Max R_{θJA} = 165 °C/W when
mounted on min pad area of
2 oz. Cu.

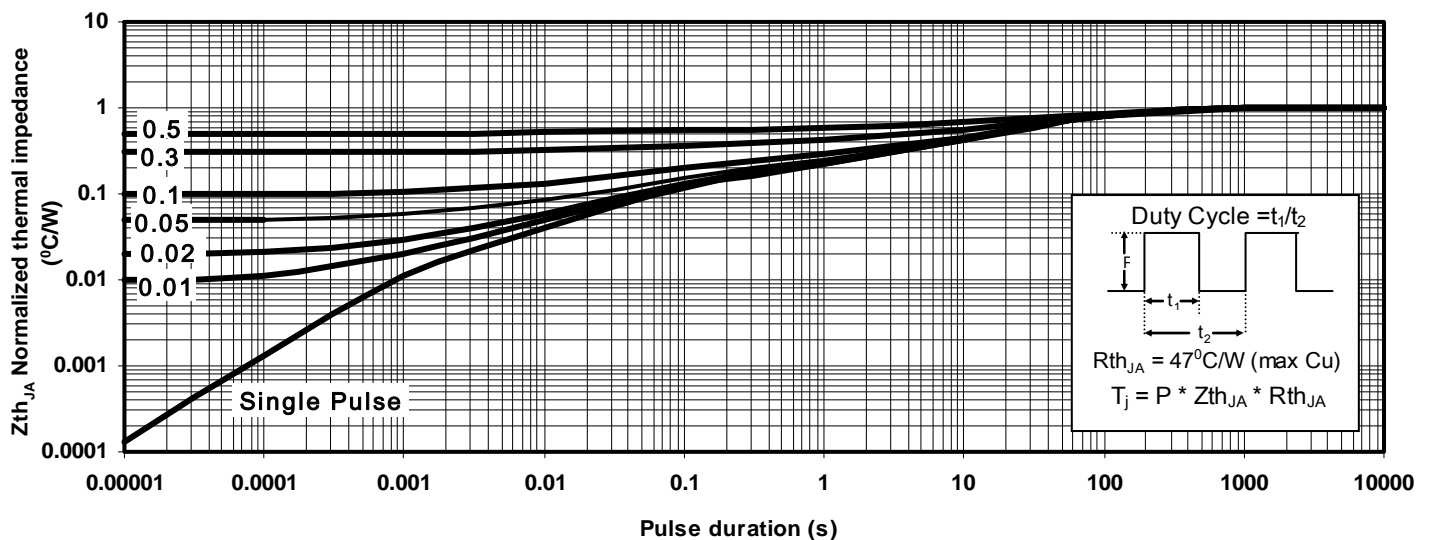


Figure 1: Transient Thermal Impedance

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Typical MOSFET Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise stated)

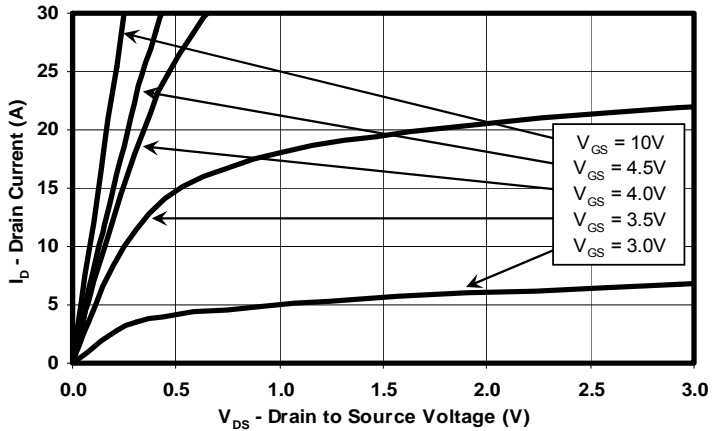


Figure 2: Saturation Characteristics

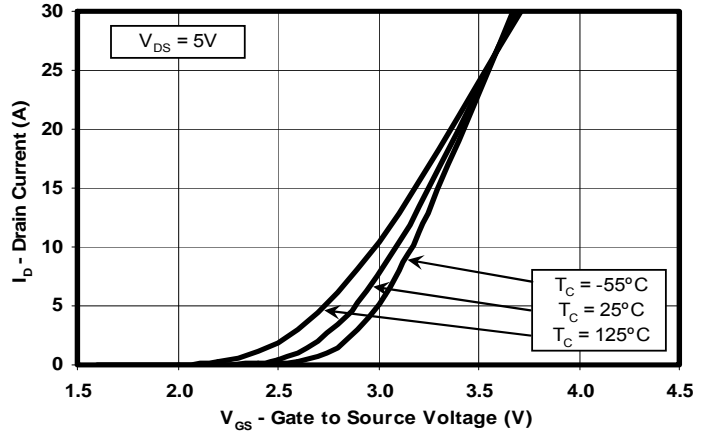


Figure 3: Transfer Characteristics

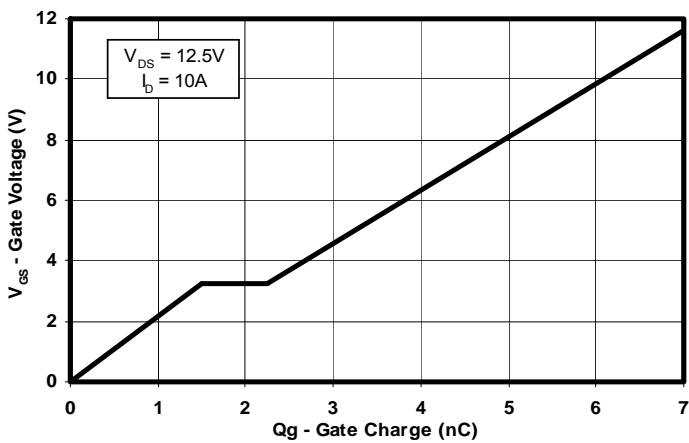


Figure 4: Gate Charge

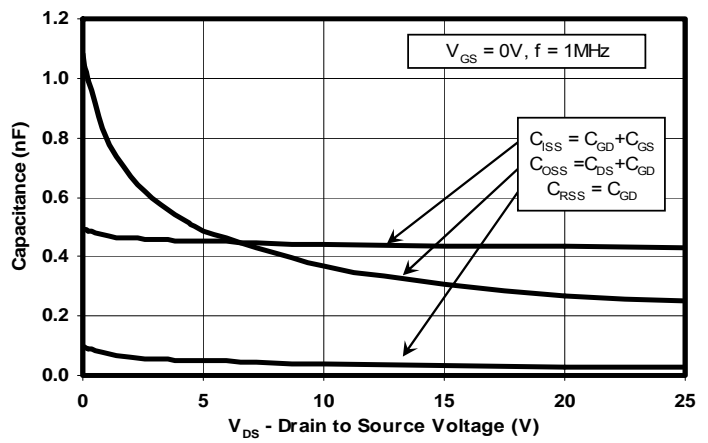


Figure 5: Capacitance

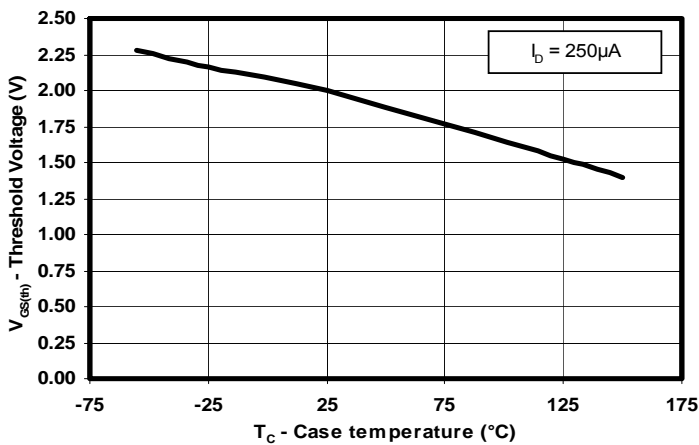


Figure 6: Threshold Voltage vs. Temperature

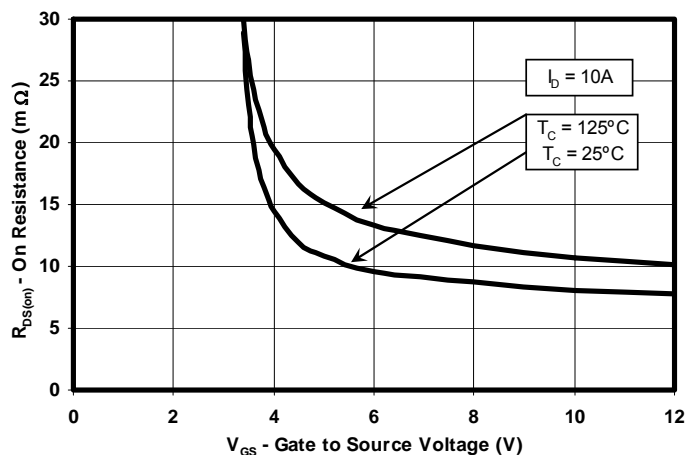


Figure 7: On Resistance vs. Gate Voltage

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Typical MOSFET Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise stated)

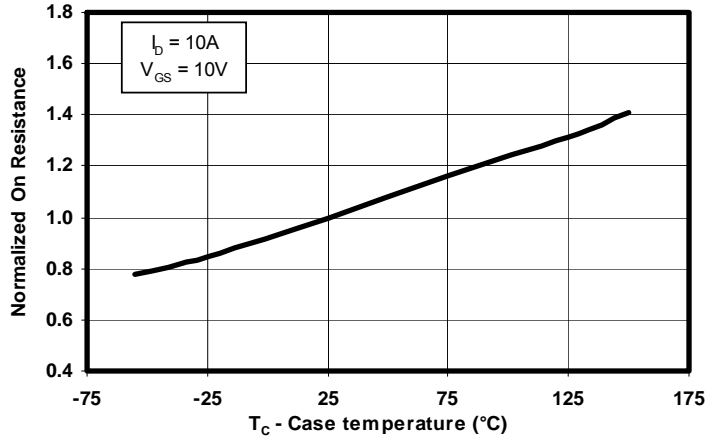


Figure 8: On Resistance vs. Temperature

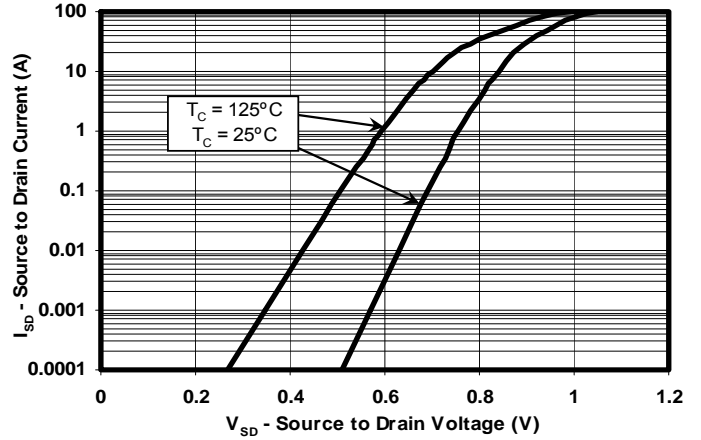


Figure 9: Typical Diode Forward Voltage

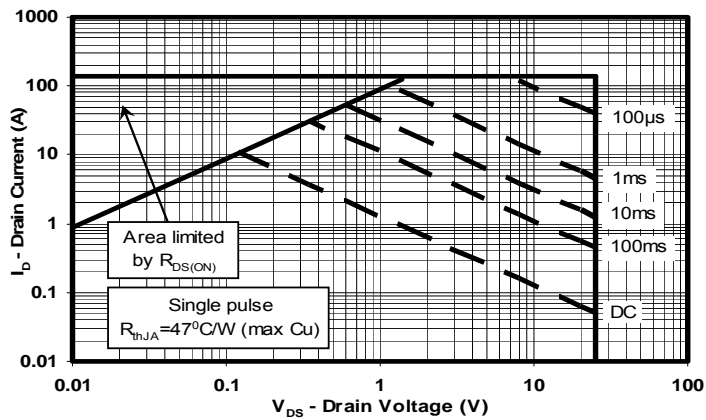


Figure 10: Maximum Safe Operating Area

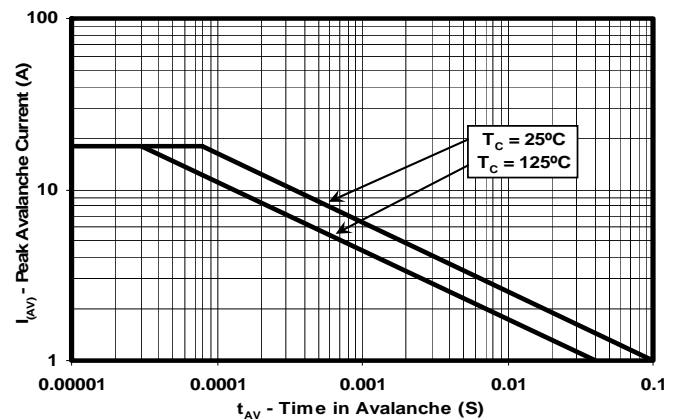


Figure 11: Single Pulse Unclamped Inductive Switching

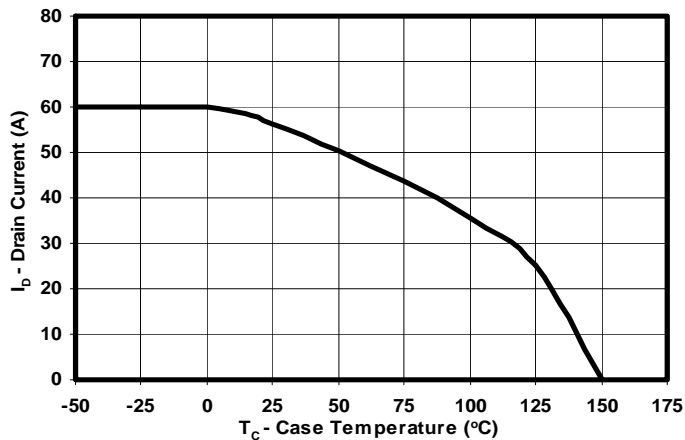
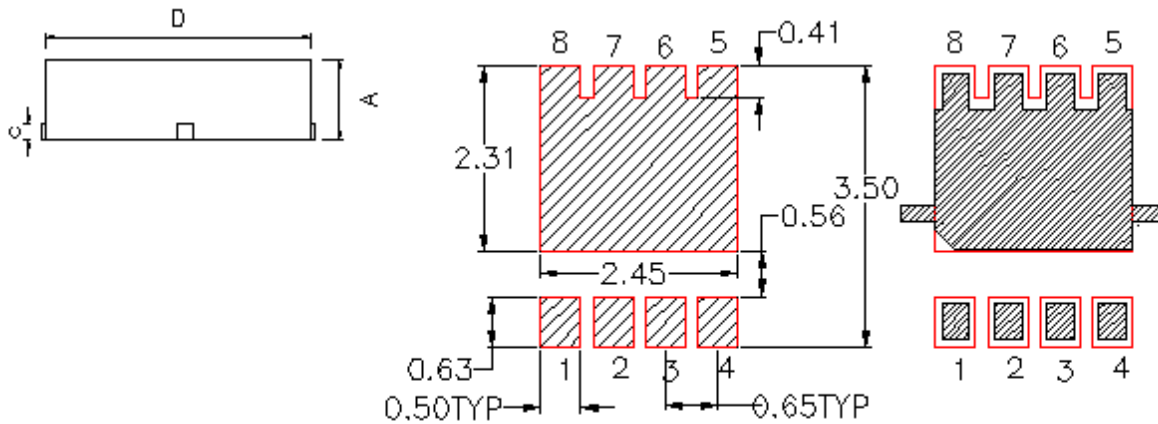
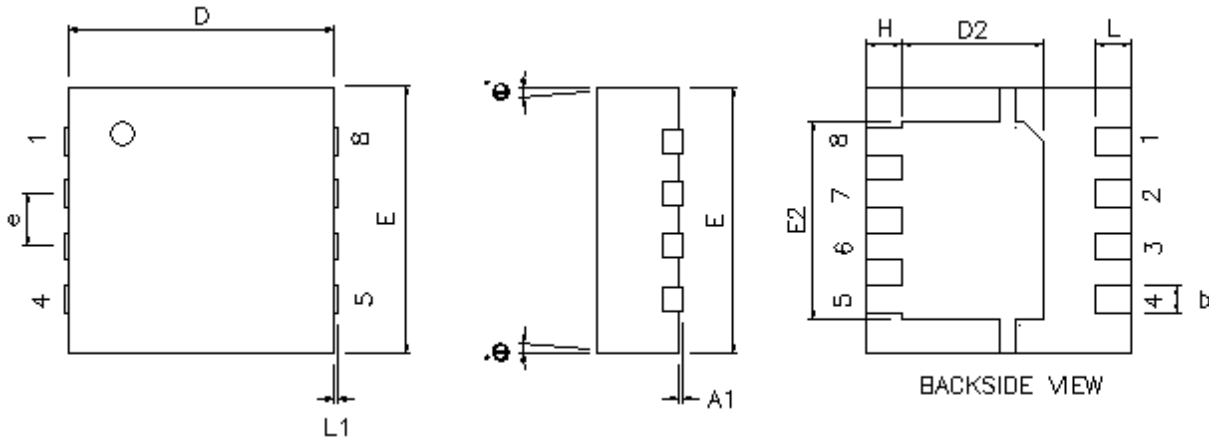


Figure 12: Maximum Drain Current vs. Temperature

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Q3 Package Dimensions



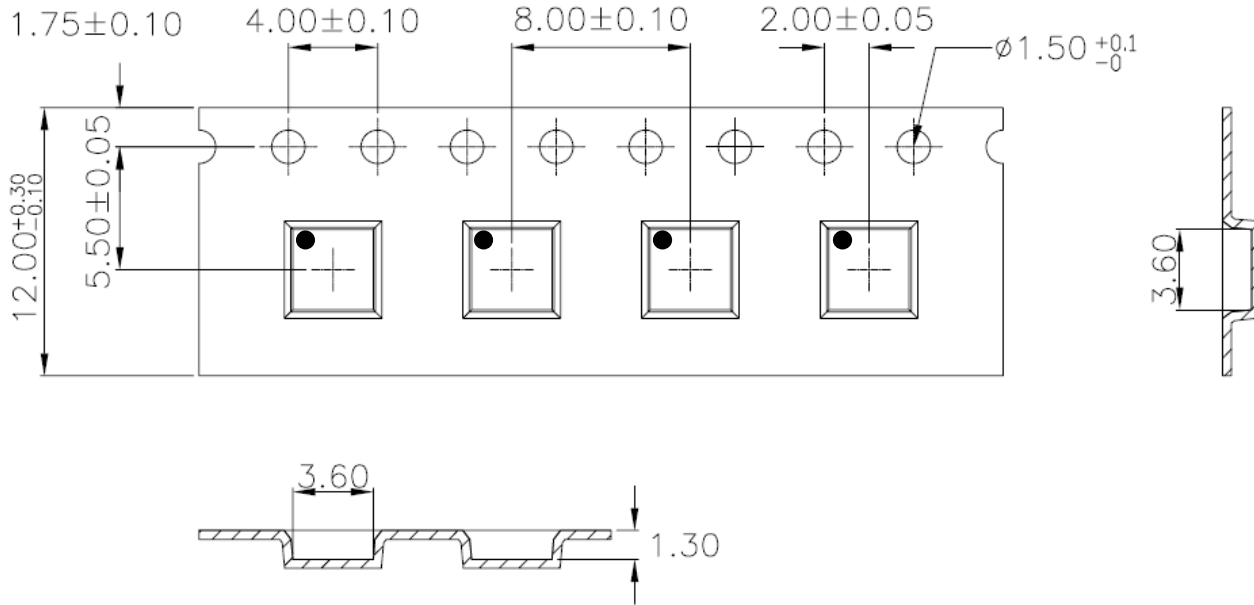
RECOMMENDED PCB LAND PATTERN

DIM	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	-	-	-	-	-	-
D2	1.650	1.750	1.800	0.065	0.069	0.071
E	3.200	3.300	3.400	0.126	0.130	0.134
E1	-	-	-	-	-	-
E2	2.350	2.450	2.550	0.093	0.096	0.100
e	0.650 TYP			0.026		
H	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	-	-	-	-	-	-
θ	-	-	-	-	-	-

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Q3 Tape and Reel Information



Note:

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE +/-0.2
2. CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm
3. MATERIAL:BLACK STATIC DISSIPATIVE POLYSTYRENE
4. ALL DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED)
5. THICKNESS: 0.30 +/-0.05mm

Package Marking Information

Location:

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

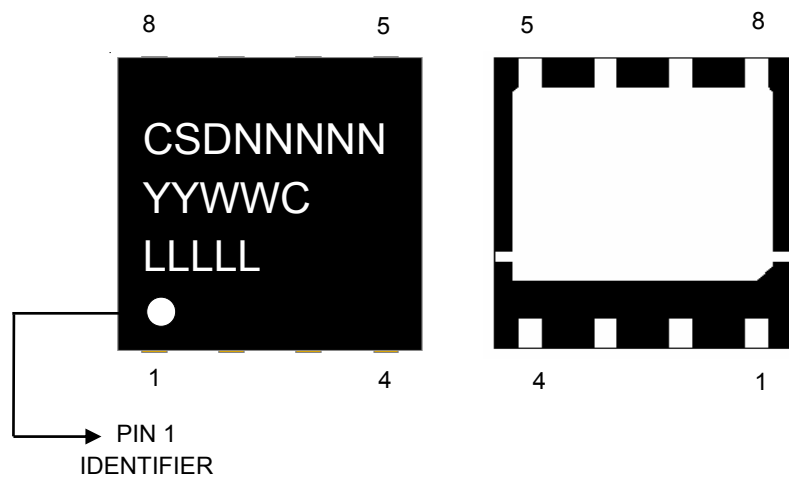
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLLL = Last 5 digits of the Wafer Lot #



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Additional Information

For further information on technology, delivery terms and conditions, or pricing please contact your nearest **CICLON** Semiconductor representative.

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